

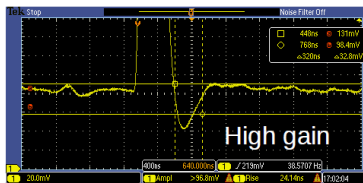
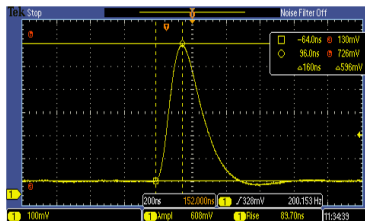
SAMPA: MPW1 test results their impact on the MPW2

Hugo Hernandez

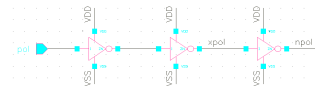
Electrical Engineering Department of the Polytechnic School,
University of São Paulo, Brazil
Institute of Physics, University of Sao Paulo, Brazil

April 1, 2015

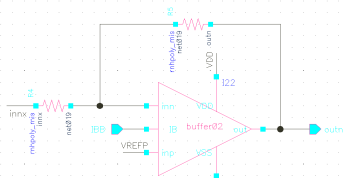
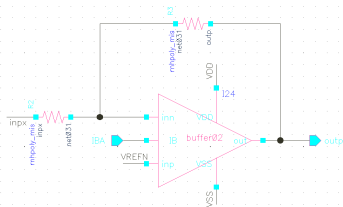
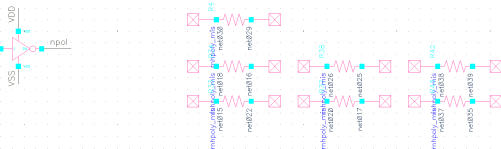
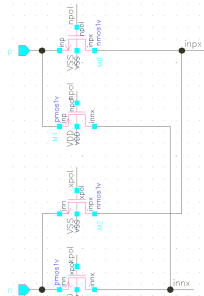
Negative Polarity undershoot



Negative Polarity undershoot: Solution



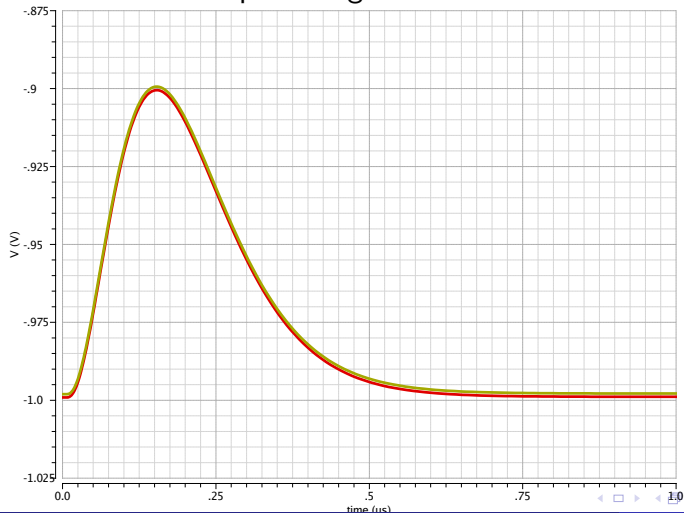
- REFP
- REFN
- VDD
- VSS



Neg/Pos Polarity undershoot: Solution

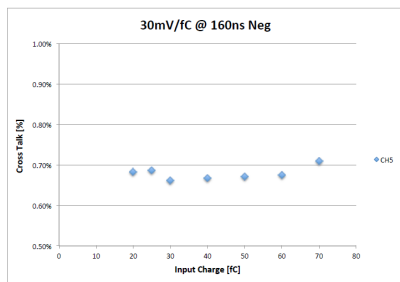
160ns@30mV

view: extracted Input charge=5fC



Crosstalk : 0.7%

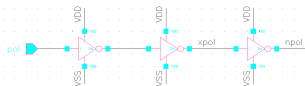
xTalk vs Input charge (4<->5)



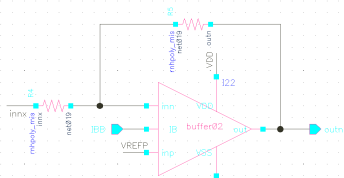
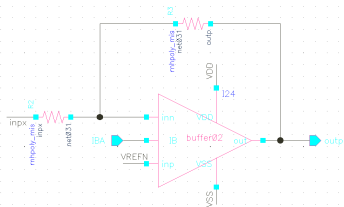
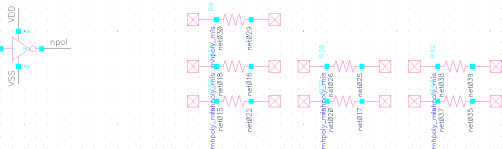
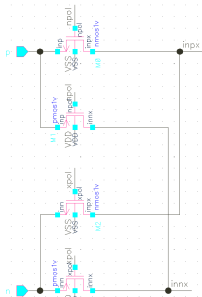
11/03/15

6

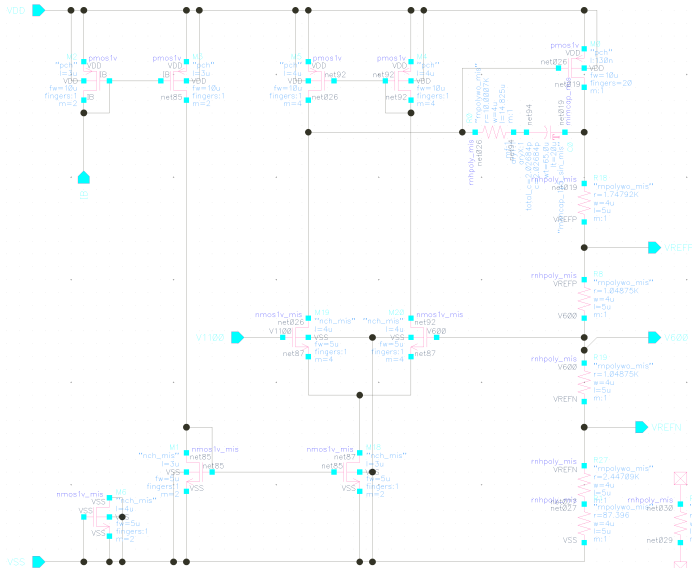
Crosstalk: partial Solution



- REFP
- REFN
- VDD
- VSS



Crosstalk: partial Solution



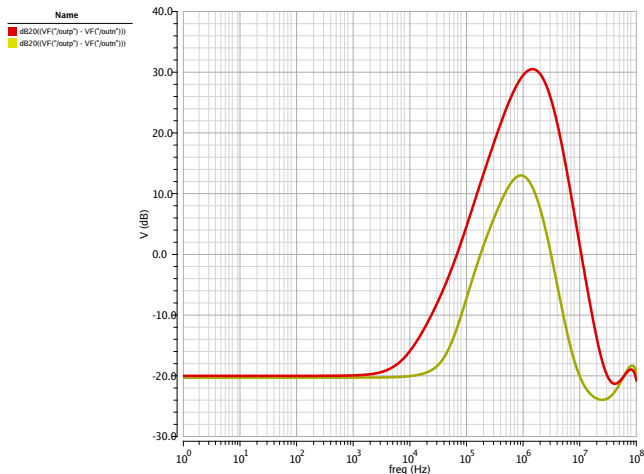
Crosstalk: actions

- Simulations including more package effects: Mutual inductance
- Reduce the bond-wire length: Chip01 (MPW1) presents long bondwire ($\approx 5\text{mm}$).
- Minimize crosstalk due to IR drop and finite PSRR.
- The GBW of the CSA was increased to reduce the input impedance (from 35Ω to 20Ω).

Chip 01: Power Supply Rejection Ratio (PSRR)

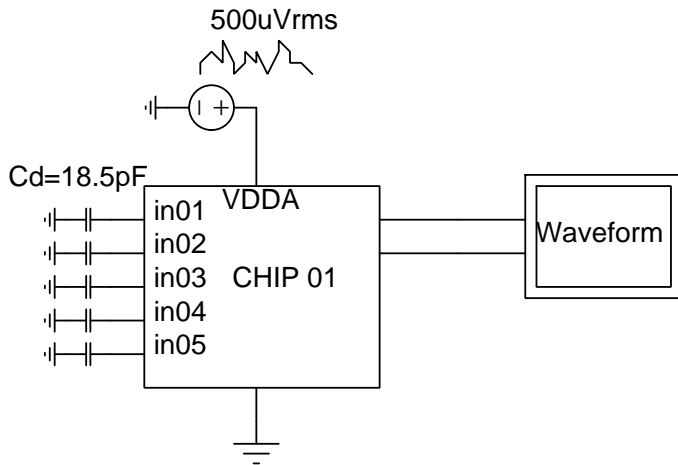
160ns 30mV/fC \Rightarrow RED

300ns 4mV/fC \Rightarrow YELLOW;



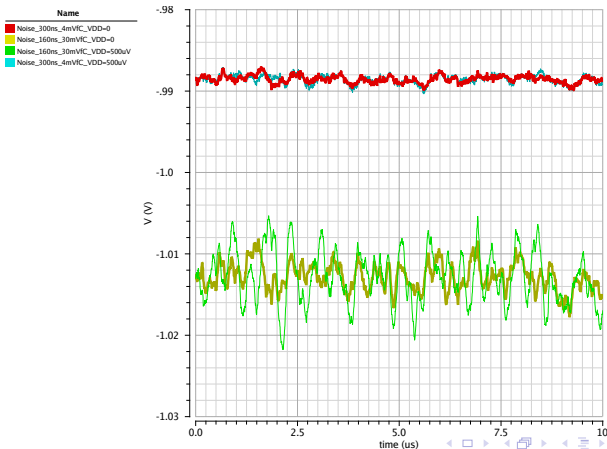
Transient noise simulation

$F_{min}=1\text{kHz}$ $F_{max}=100\text{MHz}$



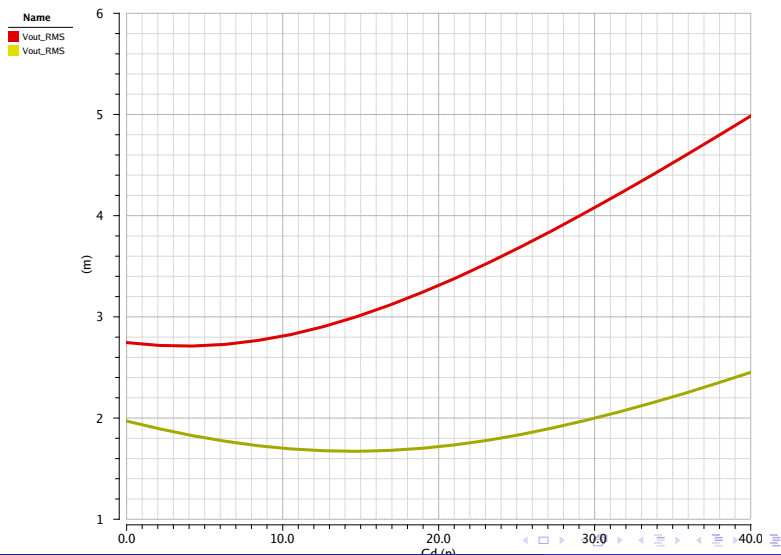
Result: Transient noise simulation

Supply Voltage Noise	VDD=0 Vrms	VDD=500 uVrms
300ns 4mV/fC	472 uVrms 736e	528 uVrms 823e
160ns 30mV/fC	1.78 mVrms 370e	3.21 mVrms 667e

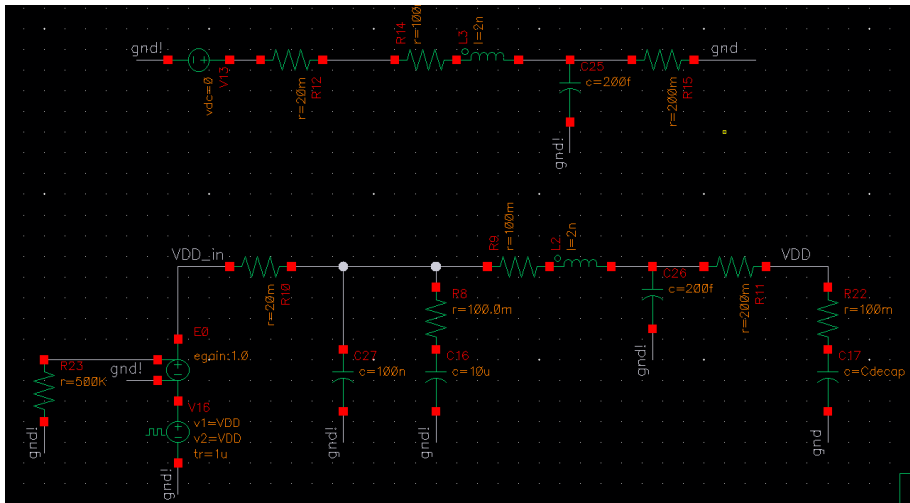


Vrms Vs Cd 160ns@30mVfC

RED: with VDD noise **YELLOW:** without VDD noise



Noise model of the supply voltage



Front-end Output noise VS DeCap (per channel)

Configuration: 160ns@30mV/fC

view: extracted

Number of channel: 16

Cap	Vrms
10pF	3.5mV
100pF	1.95mV
150pF	1.84mV
250pF	1.84mV

from MPW1 to MPW2: what has changed ?

- Front-end: Non-inverter stage (undershoot problem, crosstalk)
- Front-end: CSA (reduce the input impedance)
- Front-end: All NMOS of the front-end was implemented with triple-well (noise isolation).
- ADC: custom cells of the digital part (TSMC cells were validated)
- ADC: asynchronous to synchronous (reduce power of the reference circuits)
- ADC: Capacitor Array (reduce power of the reference circuits)
- ADC: onchip reference buffer
- System: Bandgap, 0.6Vto1.1V circuit